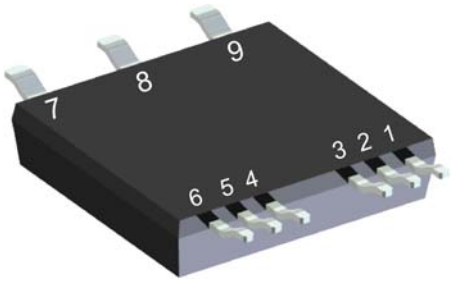
Standard Rectifier

3~ Rectifier		
V_{RRM}	=	1800 V
I_{DAV}	=	90 A
I_{FSM}	=	350 A

ISOPLUS™
Surface Mount Power Device
3~ Rectifier Bridge

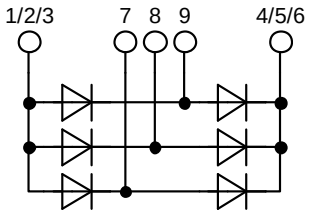
Part number

DMA90U1800LB



Backside: isolated

E72873



Features / Advantages:

- Rectifier diode
- Isolated back surface
- Low coupling capacity between pins and heatsink
- Enlarged creepage towards heatsink
- Application friendly pinout
- Low inductive current path
- High reliability

Applications:

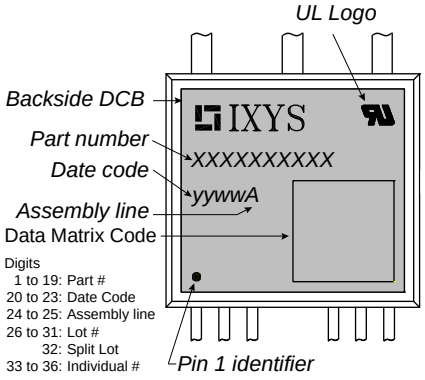
- Line rectifying 50/60 Hz
- Drives
- SMPS
- UPS

Package: SMPD

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1900	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1800	V
I_R	*reverse current*	V_R = 1800 V	T_{VJ} = 25°C			40	µA
		V_R = 1800 V	T_{VJ} = 150°C			1.5	mA
V_F	*forward voltage drop*	I_F = 30 A	T_{VJ} = 25°C			1.26	V
		I_F = 90 A				1.79	V
		I_F = 30 A	T_{VJ} = 150°C			1.20	V
		I_F = 90 A				1.93	V
I_{DAV}	*bridge output current*	T_C = 110°C	T_{VJ} = 175°C			90	A
		rectangular d = ⅓					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 175°C			0.81	V
r_F	*slope resistance* }					12.7	mΩ
R_{thJC}	*thermal resistance junction to case*					1.1	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.4		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			135	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			350	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			380	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			300	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			320	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			615	A^2s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			600	A^2s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			450	A^2s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			425	A^2s
C_J	*junction capacitance*	V_R = 400 V; f = 1 MHz	T_{VJ} = 25°C		11		pF

Package SMPD				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal				100	A
T_{stg}	*storage temperature*			-55		150	°C
T_{VJ}	*virtual junction temperature*			-55		175	°C
Weight					8.5		g
F_C	*mounting force with clip*			40		130	N
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	1.6			mm
$d_{Spb/Apb}$			*terminal to backside*	4.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA	3000			V
		t = 1 minute		2500			V

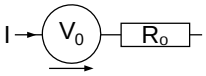


Part number

D = Diode
M = Standard Rectifier
A = (up to 1800V)
90 = Current Rating [A]
U = 3~ Rectifier Bridge
1800 = Reverse Voltage [V]
LB = SMPD-B

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DMA90U1800LB	DMA90U1800LB	Blister	45	511747
Alternative	DMA90U1800LB-TRR	DMA90U1800LB	Tape & Reel	200	511740

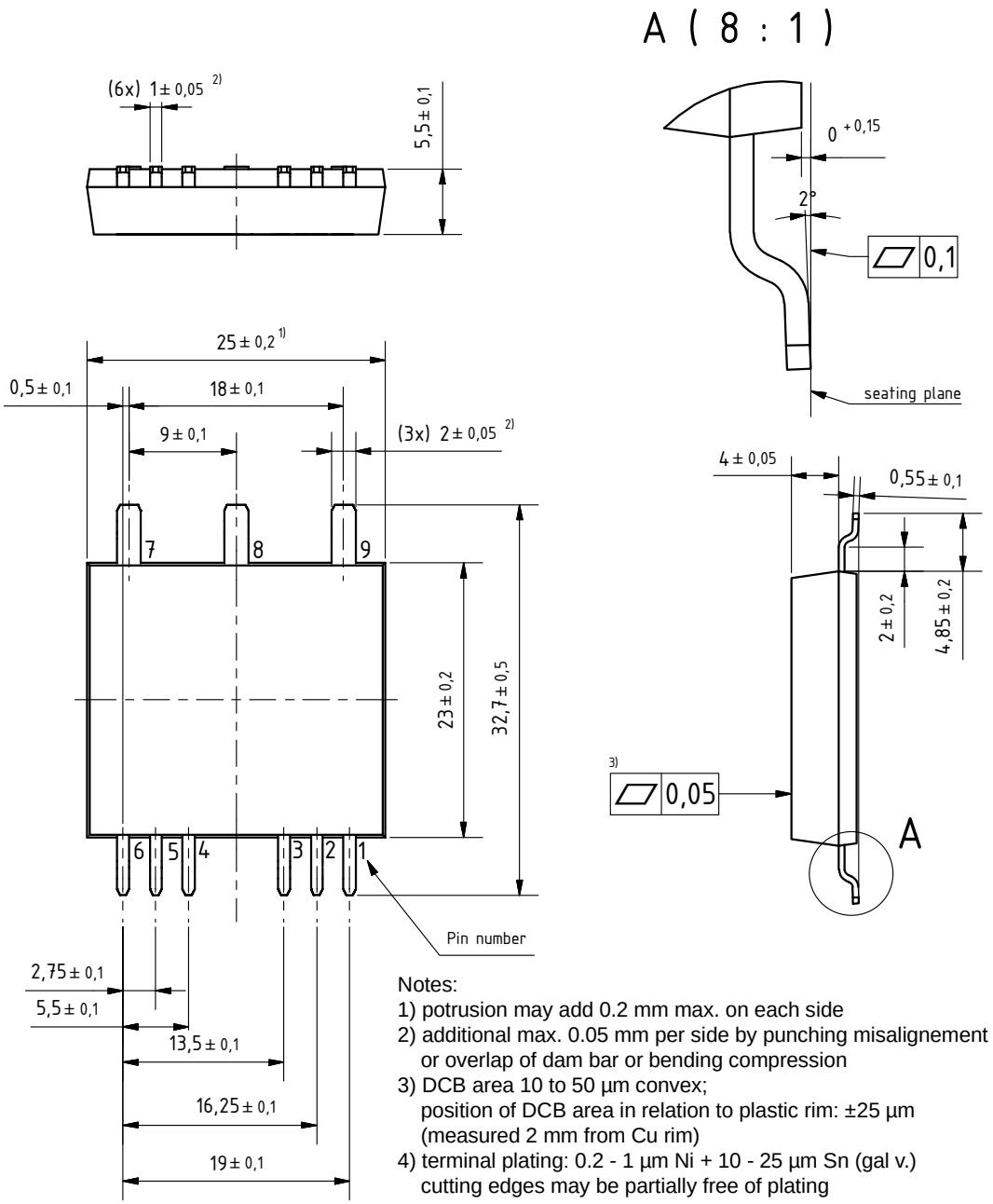
Equivalent Circuits for Simulation ** on die level* T_{VJ} = 175 °C



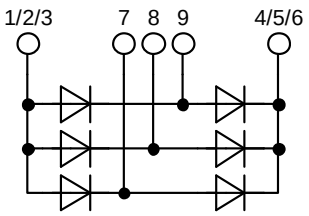
Rectifier

$V_{0\,max}$	*threshold voltage*	0.81	V
$R_{0\,max}$	*slope resistance **	10.1	mΩ

Outlines SMPD



Notes:
1) potrusion may add 0.2 mm max. on each side
2) additional max. 0.05 mm per side by punching misalignement or overlap of dam bar or bending compression
3) DCB area 10 to 50 µm convex;
position of DCB area in relation to plastic rim: ±25 µm (measured 2 mm from Cu rim)
4) terminal plating: 0.2 - 1 µm Ni + 10 - 25 µm Sn (gal v.)
cutting edges may be partially free of plating



Rectifier

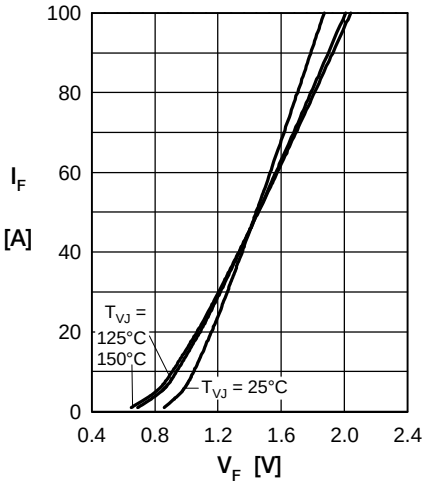


Fig. 1 Forward current vs. voltage drop per diode

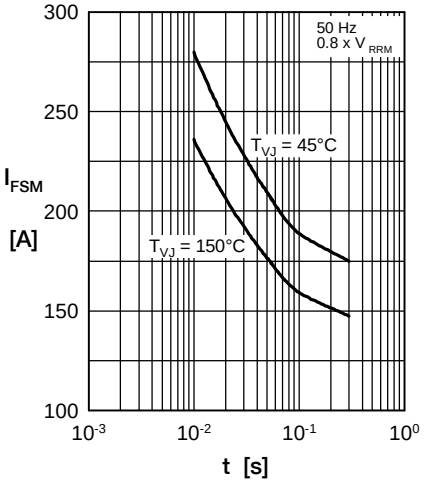


Fig. 2 Surge overload current vs. time per diode

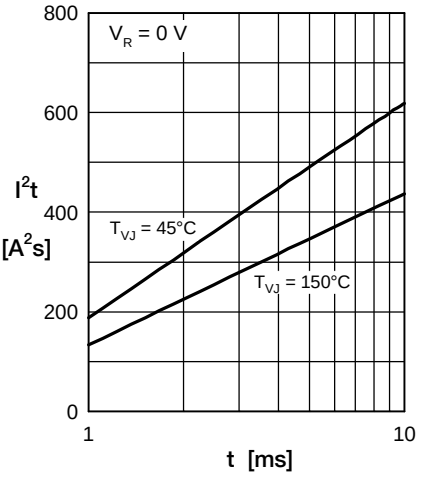


Fig. 3 I^2t vs. time per diode

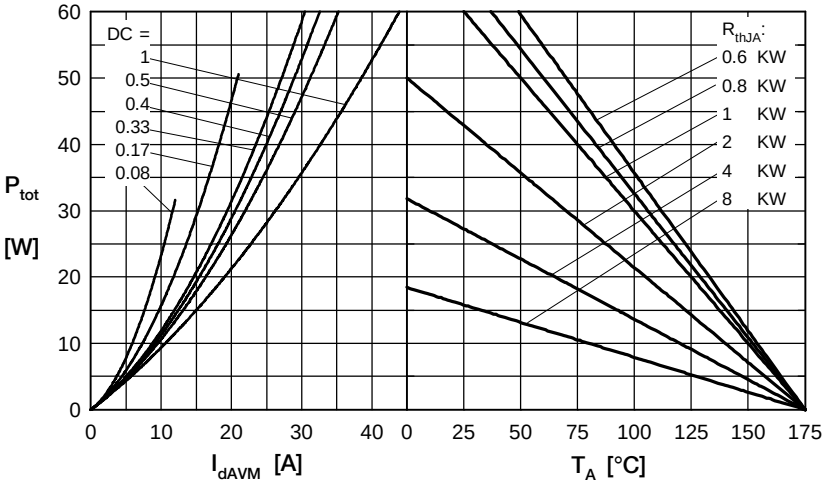


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

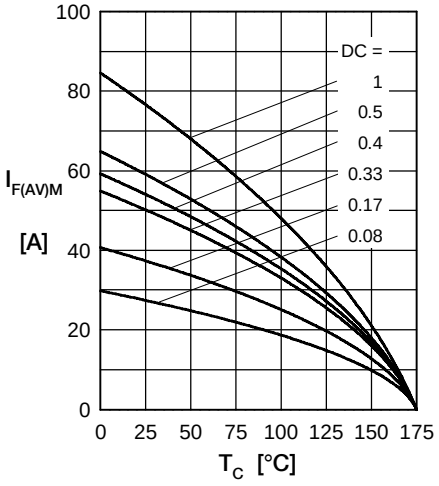


Fig. 5 Max. forward current vs. case temperature per diode

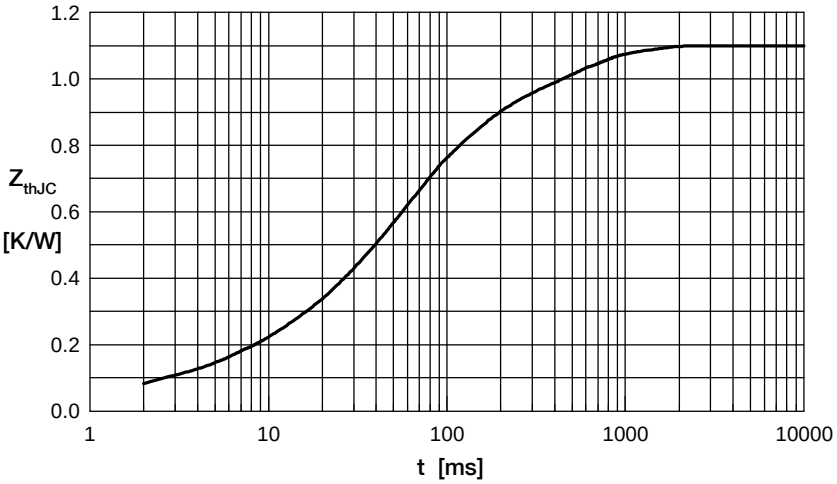


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.030	0.0003
2	0.072	0.0045
3	0.092	0.0530
4	0.606	0.0520
5	0.300	0.4000